

■ **N-Channel Enhancement MOSFET**

■ **Features**

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

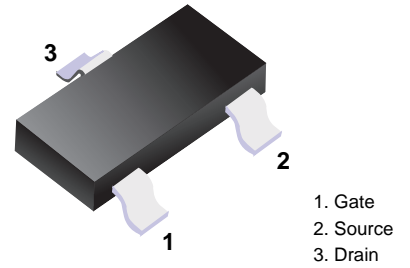
■ **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

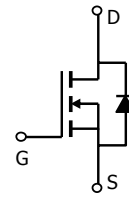
■ **Description**

The KF1003 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

It is ESD protected.



■ **Simplified outline(SOT23-3L)**



V_{DSS}	$R_{DS(ON)}$ @10V (typ)	I_D
100V	135mΩ	5A

■ **MARKING**

Marking	G1003A
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■ **Absolute Maximum Ratings** $T_a = 25^\circ\text{C}$

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	24	A
Maximum Power Dissipation	P_D	5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

■ **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	$^\circ\text{C/W}$
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■ Electrical Characteristics Ta = 25°C

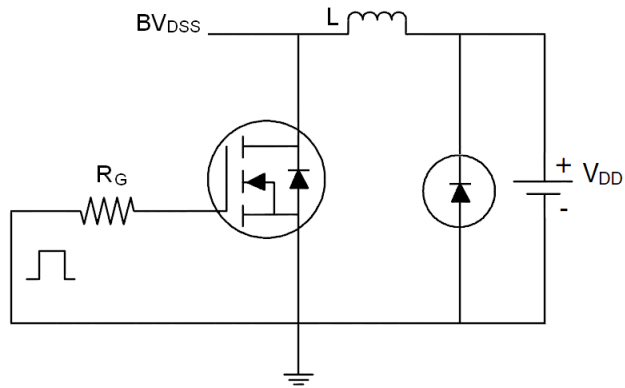
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	105	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	800	nA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 30	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	2	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$	-	135	145	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=2.9A$	-	8	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	690	-	PF
Output Capacitance	C_{OSS}		-	120	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	7.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	t_f		-	9.1	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=3A,$ $V_{GS}=10V$	-	15.5	-	nC
Gate-Source Charge	Q_{gs}		-	3.2	-	nC
Gate-Drain Charge	Q_{gd}		-	4.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=6A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	6	A

Notes:

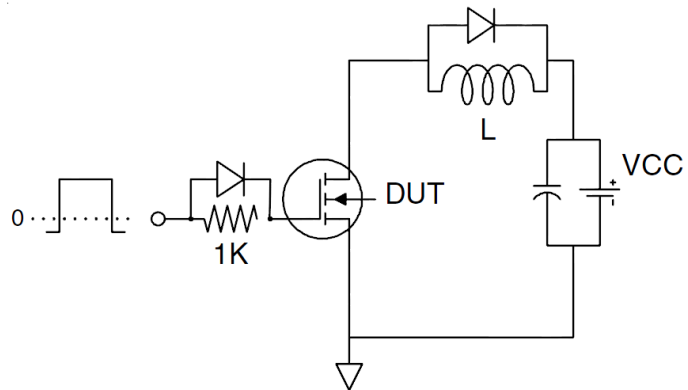
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

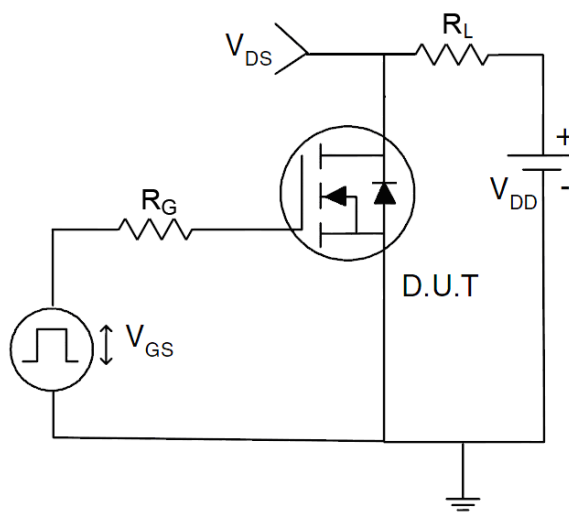
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (curves)

Figure1. Source-Drain Diode Forward Voltage

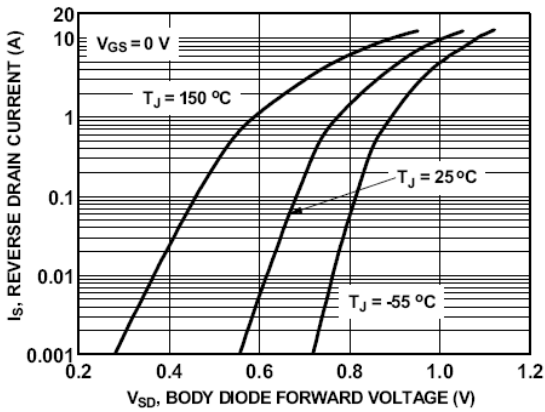


Figure2. Safe operating area

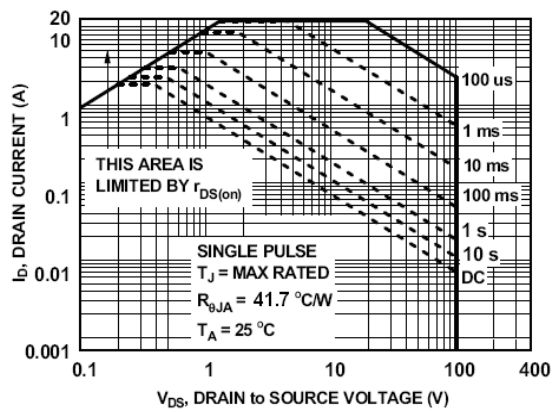


Figure3. Output characteristics

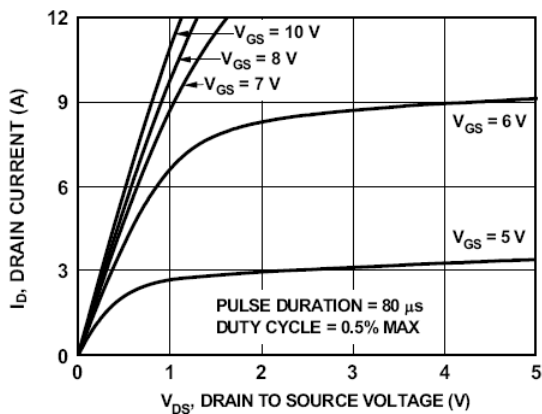


Figure4. Transfer characteristics

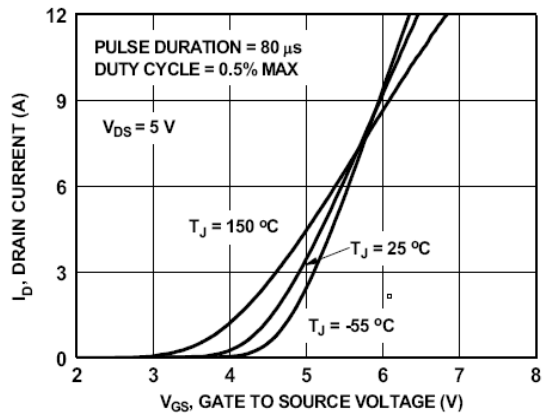


Figure5. Static drain-source on resistance

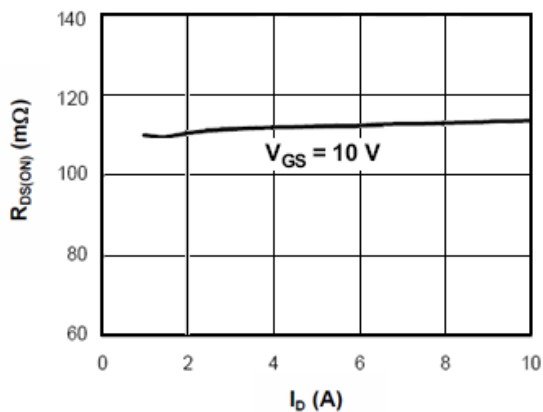


Figure6. $R_{DS(ON)}$ vs Junction Temperature

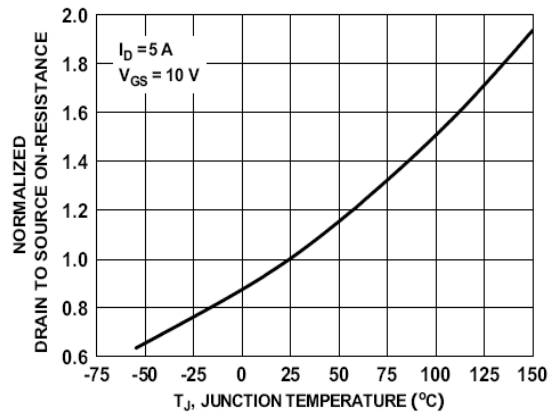


Figure7. BV_{DSS} vs Junction Temperature

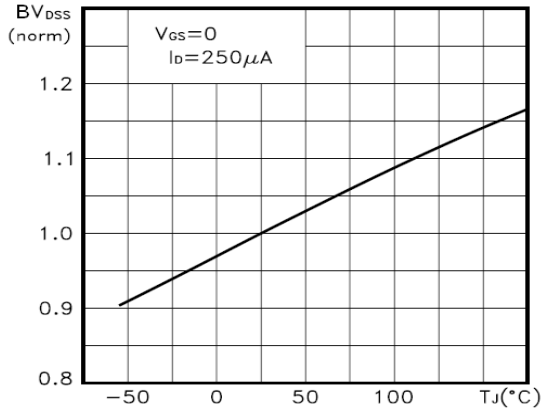


Figure8. V_{GS(th)} vs Junction Temperature

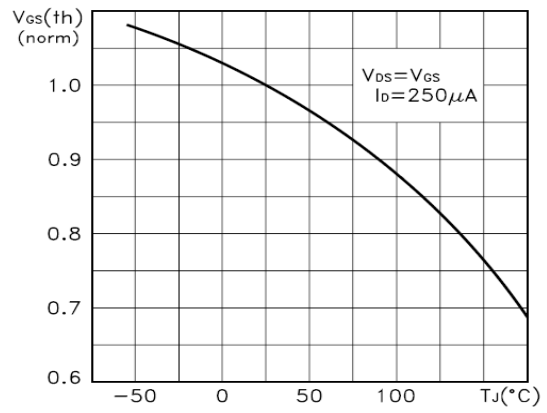


Figure9. Gate charge waveforms

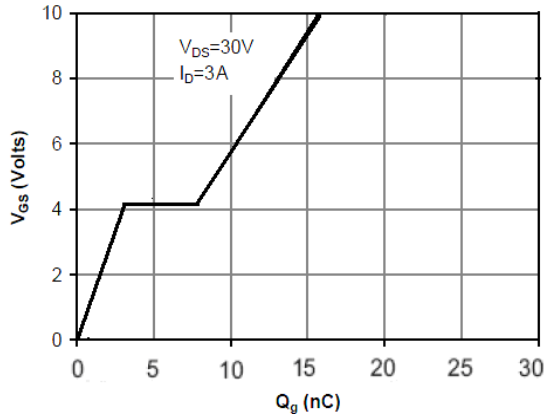


Figure10. Capacitance

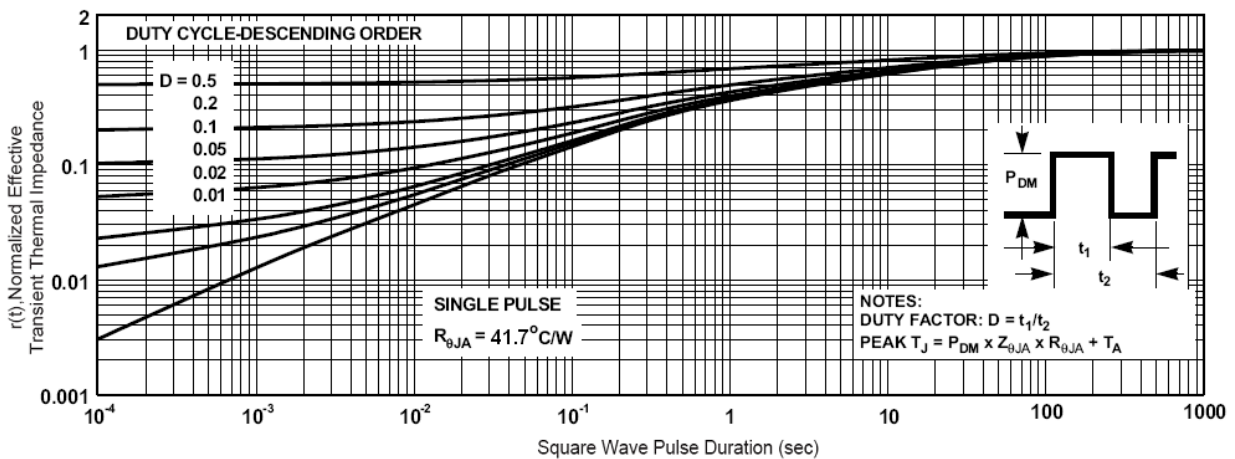
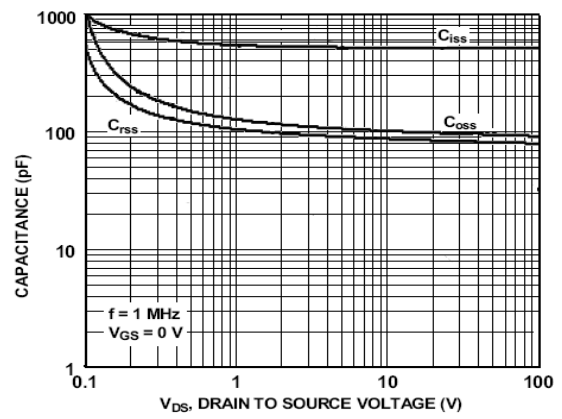
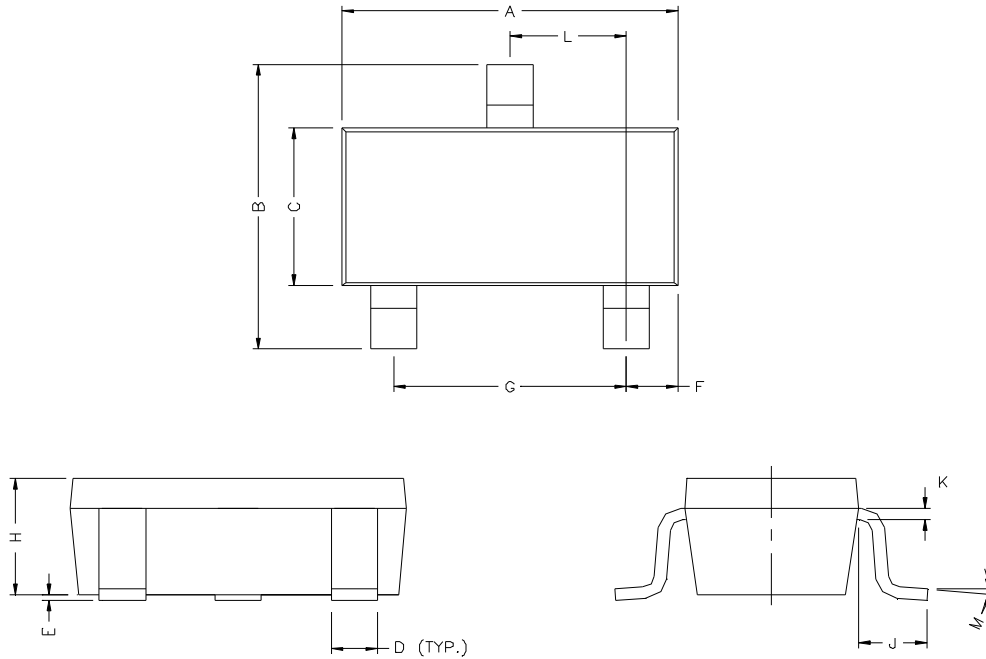


Figure11. Normalized Maximum Transient Thermal Impedance

Package Outline

SOT23-3L



DIMENSIONS (mm are the original dimensions)

UNIT	A	B	C	D	E	F	G	H	K	J	L	M
mm	2.70 3.10	2.65 2.95	1.50 1.70	0.35 0.50	0 0.10	0.45 0.55	1.9	1.00 1.30	0.10 0.20	0.40 -	0.85 1.15	0° 10°

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT23-3L	Tape/Reel, 7" reel	3000	EIA-481-1